



## 1N70K-TA

Preliminary

Power MOSFET

### 1.2A, 700V N-CHANNEL POWER MOSFET

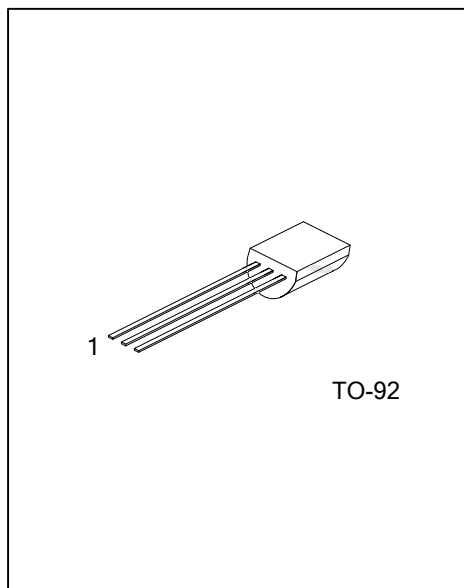
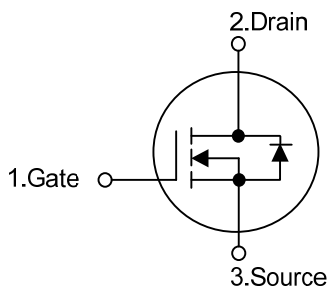
#### DESCRIPTION

The UTC **1N70K-TA** is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

#### FEATURES

- \*  $R_{DS(ON)} < 13.5\Omega @ V_{GS} = 10V, I_D = 0.5A$
- \* Fast switching capability
- \* Avalanche energy specified
- \* Improved dv/dt capability, high ruggedness

#### SYMBOL



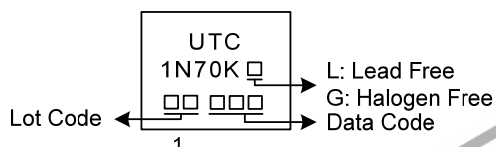
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
1N70KL-x-T92-B	1N70KG-x-T92-B	TO-92	G	D	S	Tape Box
1N70KL-x-T92-K	1N70KG-x-T92-K	TO-92	G	D	S	Bulk

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>1N70KL-T92-B</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) B: Tape Box, K: Bulk (2) T92: TO-92 (3) L: Lead Free, G: Halogen Free and Lead Free</p>
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#### MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	700	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Continuous Drain Current	Continuous	$I_D$	1.0	A
Pulsed Drain Current	Pulsed (Note 2)	$I_{DM}$	4.0	A
Avalanche Current (Note 2)		$I_{AR}$	1.0	A
Single Pulsed Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	5	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation		$P_D$	1.6	W
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3.  $L = 10\text{mH}$ ,  $I_{AS} = 1.0\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD} \leq 1.0\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$ .

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	140	$^\circ\text{C}/\text{W}$
Junction to Case	$\theta_{JC}$	80	$^\circ\text{C}/\text{W}$

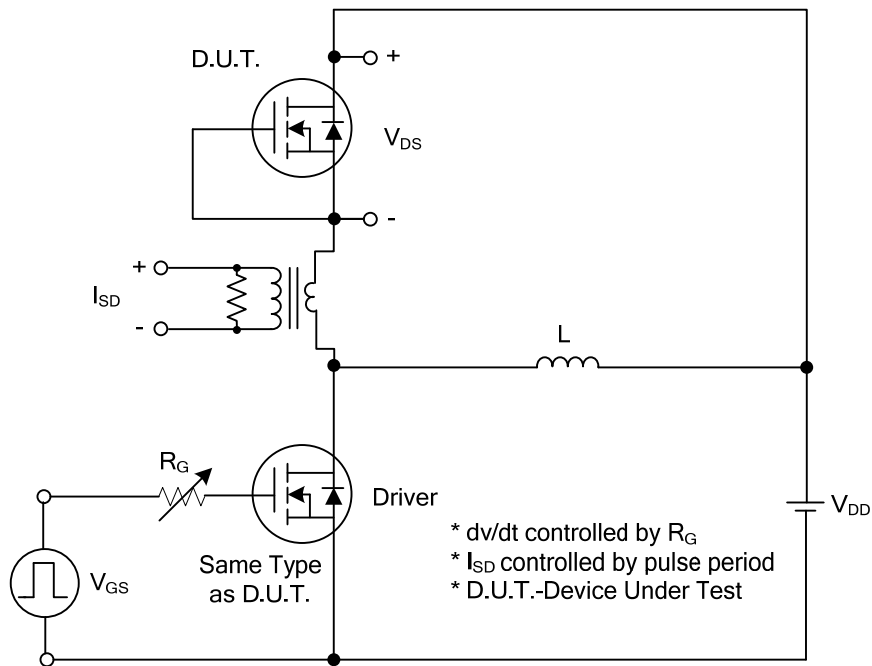
■ ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0\text{V}$ , $I_D = 250\mu\text{A}$	700			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 700\text{V}$ , $V_{GS} = 0\text{V}$			1	$\mu\text{A}$
Gate-Source Leakage Current	Forward	$I_{GSS}$ $V_{GS} = 30\text{V}$ , $V_{DS} = 0\text{V}$			100	nA
	Reverse				-100	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}$ , $I_D = 0.5\text{A}$			13.5	$\Omega$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{ISS}$	$V_{DS}=25\text{V}$ , $V_{GS}=0\text{V}$ , $f=1\text{MHz}$		190		pF
Output Capacitance	$C_{OSS}$			25		pF
Reverse Transfer Capacitance	$C_{RSS}$			10		pF
<b>SWITCHING CHARACTERISTICS</b>						
Rise Time (Note 1)	$Q_G$	$V_{DS}=50\text{V}$ , $V_{GS}=10\text{V}$ , $I_D=1.3\text{A}$ , $I_G=100\mu\text{A}$ (Note 1, 2)		14		nC
Turn-OFF Delay Time	$Q_{GS}$			2.8		nC
Fall-Time	$Q_{GD}$			1		nC
Total Gate Charge (Note 1)	$t_{D(ON)}$	$V_{DD}=30\text{V}$ , $V_{GS}=10\text{V}$ , $I_D=0.5\text{A}$ , $R_G=25\Omega$ (Note 1, 2)		35		ns
Gate to Source Charge	$t_R$			20		ns
Gate to Drain Charge	$t_{D(OFF)}$			45		ns
Turn-ON Delay Time	$t_F$			8		ns
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Body-Diode Continuous Current	$I_S$				1.0	A
Maximum Body-Diode Pulsed Current	$I_{SM}$				4.0	A
Drain-Source Diode Forward Voltage (Note 1)	$V_{SD}$	$I_S=1.0\text{A}$ , $V_{GS}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	$t_{rr}$	$I_S=1.0\text{A}$ , $V_{GS}=0\text{V}$ ,		310		nS
Body Diode Reverse Recovery Charge	$Q_{rr}$	$di/dt=100\text{A}/\mu\text{s}$		0.65		$\mu\text{C}$

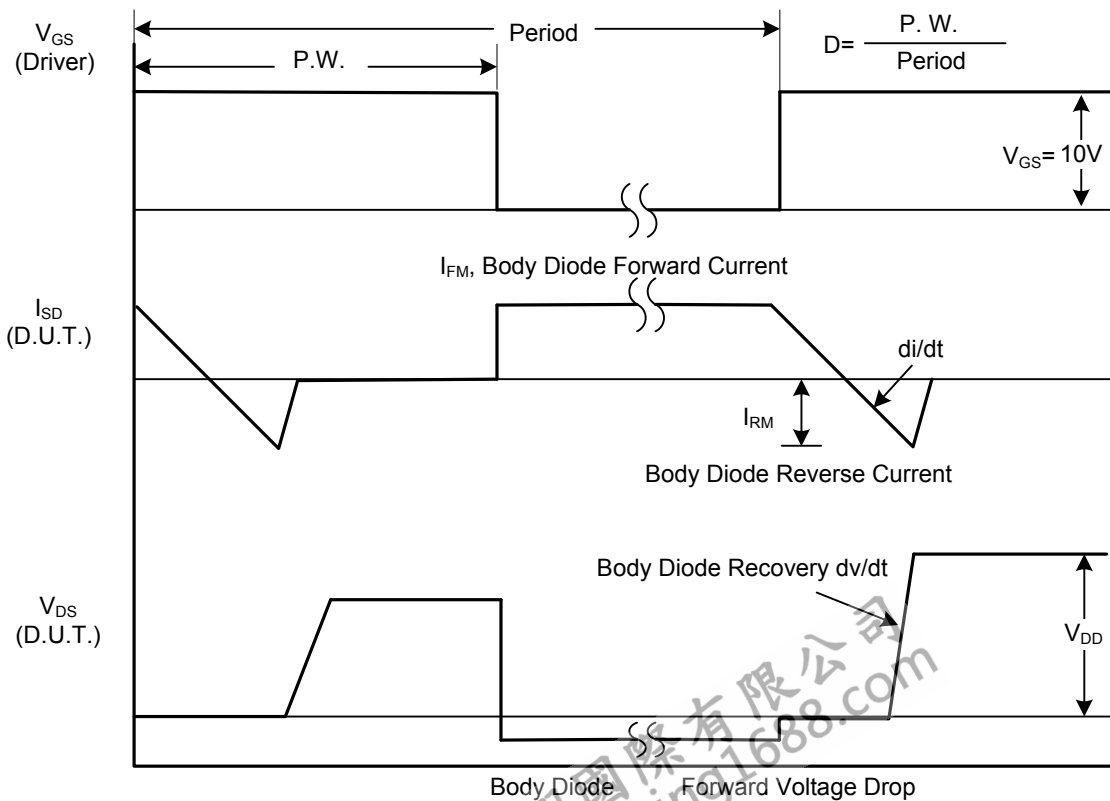
Notes: 1. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$ .

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

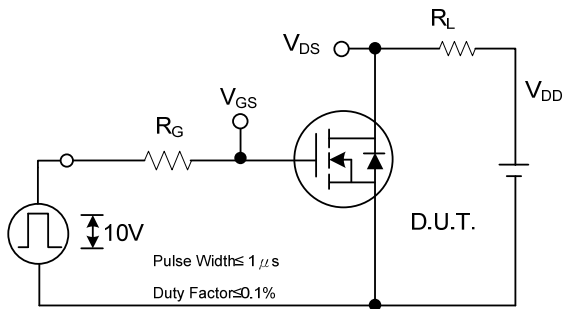


Peak Diode Recovery  $dv/dt$  Test Circuit

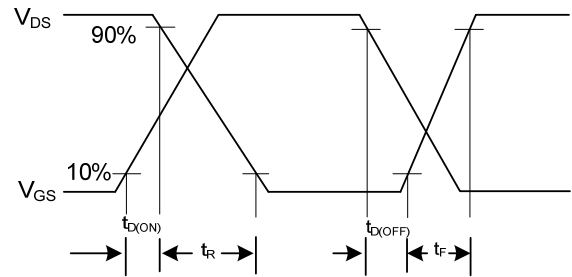


Peak Diode Recovery  $dv/dt$  Waveforms

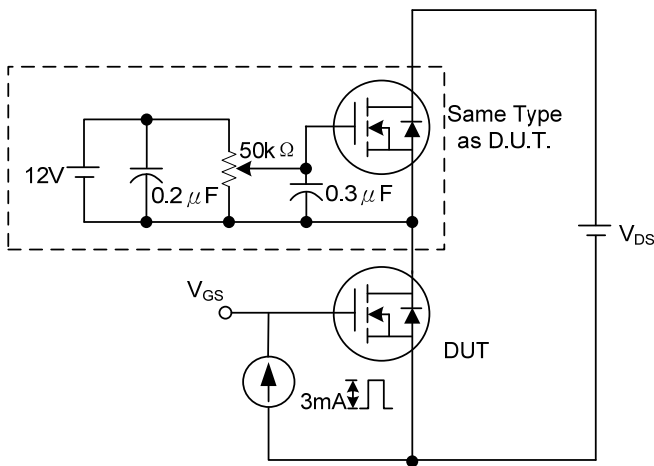
### TEST CIRCUITS AND WAVEFORMS (Cont.)



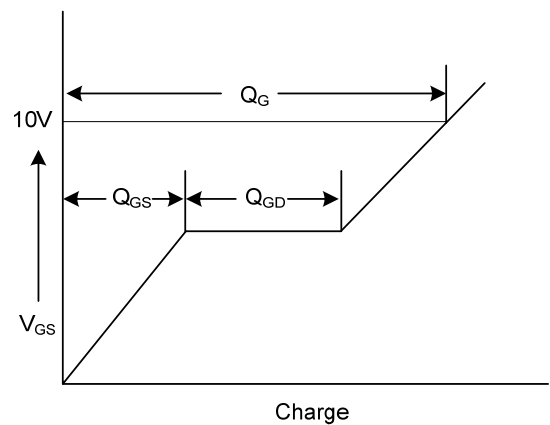
**Switching Test Circuit**



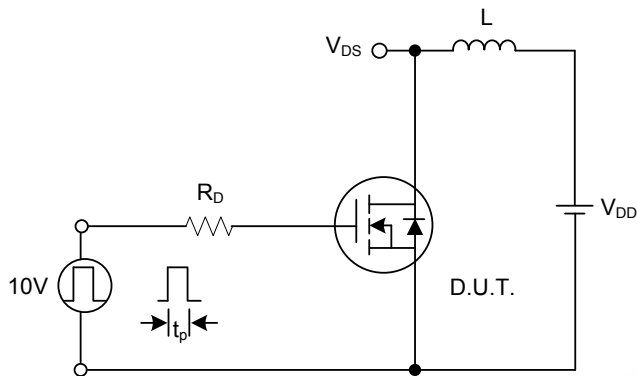
**Switching Waveforms**



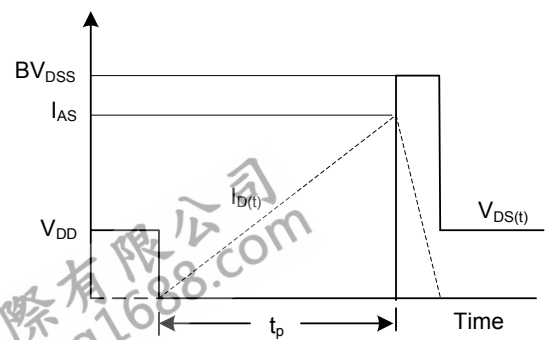
**Gate Charge Test Circuit**



**Gate Charge Waveform**



**Unclamped Inductive Switching Test Circuit**



**Unclamped Inductive Switching Waveforms**

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